

**INFORMATION DISCLOSURE
CITATION**

SERIAL NO.

160-410

10/801,038

APPLICANT

NAKAMURA et al

FILING DATE

TC/A.U.

March 16, 2004

2814

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)
 22-64419 (03/1997) together w/Abstract (12 pgs.)

OTHER DOCUMENTS (including Author, Title, Date, Pertinent pgs.)	
TD	Computer English Translation of JP 9-64419 (03/1997) together w/Abstract (12 pgs.)
TD	Computer English Translation of JP 8-293643 (11/1996) together w/Abstract (15 pgs.)
TD	Computer English Translation of JP 7-249795 (09/1995) together w/Abstract (14 pgs.)
TD	KUGA et al., "Violet and Near-UV Light Emission from GaN/Al _{0.08} Ga _{0.92} N Injection Diode Grown on (0001) 6H-SiC Substrate by Low-Pressure Metal-Organic Vapor Phase Epitaxy," Jpn. J. Appl. Phys., Vol. 34, Part 1, No. 8A (1995), pp. 4085-4086

/Theresa Doan/

Date Considered _____

08/29/2006

*Examiner	/Theresa Doan/	Date Considered	
-----------	----------------	-----------------	--

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.

488893

1088997